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Power Matters.

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2N5092 (#23281)

Product Status

In Production

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Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			0.50	V
DC Current Gain	HFE	50.00		300.00	

Maximum Electrical Rating	Symbol	Min	Тур	Мах	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			400.00	V
Collector Current (dc)	Ic			1.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			400.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			6.00	٧
Power Dissipation, Total	P _T			4.00	W

This part can be found in the following product categories:

Power Discretes & Modules ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor

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